

Spectral changes in layered f -electron systems induced by Kondo hole substitution in the boundary-layer

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We investigate the effect of disorder on the dynamical spectrum of layered f -electron systems. With random dilution of f -sites in a single Kondo insulating layer, we explore the range and extent to which Kondo hole incoherence can penetrate into adjacent layers. We consider three cases of neighboring layers: band insulator, Kondo insulator and simple metal. The disorder-induced spectral weight transfer, used here for quantification of the proximity effect, decays algebraically with distance from the boundary layer. Further, we show that the spectral weight transfer is highly dependent on the frequency range considered as well as the presence of interactions in the clean adjacent layers. The changes in the low frequency spectrum are very similar when the adjacent layers are either metallic or Kondo insulating, and hence are independent of interactions. In stark contrast, a distinct picture emerges for the spectral weight transfers across large energy scales. The spectral weight transfer over all energy scales is much higher when the adjacent layers are non-interacting as compared to when they are strongly interacting Kondo insulators. Thus, over all scales, interactions screen the disorder effects significantly. We discuss the possibility of a crossover from non-Fermi liquid to Fermi liquid behavior upon increasing the ratio of clean to disordered layers in particle-hole asymmetric systems.

1. INTRODUCTION

Several surprises have emerged through extensive experimental and theoretical investigations of layered correlated systems over the last decade. The pioneering study of Ohtomo *et al.* led to the discovery of a two-dimensional electron gas at the interface of Mott insulating LaTiO_3 and band insulating SrTiO_3 in atomically resolved heterostructures¹. A dimensional driven crossover from metal to insulator transition² and an anomalous effective mass enhancement³ was observed by Yoshimatsu *et al.* in digitally controlled SrVO_3 thin films. Theoretical predictions in this regard had been reported and semiquantitatively explained by Okamoto *et al.* in Ref. 4. An early work in this regard may also be found in Ref. 5. In general, strongly correlated interfaces exhibit several other unexpected properties such as superconductivity⁶, coexistence of ferromagnetism and superconductivity⁷, and electronic phase separation⁸. Such investigations have led to a renewed focus on a number of intriguing aspects of layered systems. Some of these issues are due to atomic reconstruction, enhanced correlation effects due to reduced coordination number and emergent energy scales owing to the presence of disparate orbital, charge, and spin degrees of freedom⁹.

A significant number of theoretical studies on the proximity effects of electron-electron interaction in layered systems have been carried out. Such studies include proximity effects in Hubbard layers^{10–18}, Falicov-Kimball layers¹⁹ or f -electron superlattices^{20,21}. Zenia *et al.*¹² demonstrated that a Mott insulator transforms to a "fragile" Fermi liquid if sandwiched between metallic leads. Helmes *et al.*¹⁷ studied interfaces of strongly correlated metals with Mott insulators. The

rate of decay of the quasiparticle weight into the Mott insulator was quantified and further corroborated in the spirit of a Ginzburg-Landau mean field treatment. Ishida and Liebsch¹⁵ investigated the effect of an interplanar Coulomb interaction using the cellular Dynamical Mean Field Theory (DMFT) and observed a non-local correlation induced reduction of the proximity effect. Cluster extensions of DMFT was employed by Okamoto *et al.* in Ref. 22 to examine the proximity effect in superlattices involving cuprates, predicting a novel enhancement in the superconducting transition temperature.

Recent experimental investigations of heavy fermion (f -electron) superlattices indicate a fascinating interplay of heavy fermion physics, low dimensionality and interface effects²³. In the heavy fermion superlattices $m\text{CeIn}_3$ - $n\text{LaIn}_3$, by reducing the thickness of the CeIn_3 layers grown on metallic LaIn_3 , it was demonstrated that the dimensionality of the f -electrons and the magnetic order could be controlled. These dimensionally confined heavy fermion systems then displayed non-Fermi liquid properties that manifested as a linear temperature dependence in resistivity, $\rho_{xx} \sim T$, with a T^2 behavior recovered on increasing the number of CeIn_3 layers. This has been followed up with very recent theoretical investigations of the Kondo effect and dimensional crossover in f -electron superlattices^{20,21,24}. Tada *et al.*²¹ analyzed the formation of heavy electrons in f -electron multilayers. They demonstrated the existence of two (in-plane and out of plane) coherence temperatures in such systems. This implies a crossover in dimensionality of the heavy fermions from two to three dimensions as the temperature and the geometry of the system change. In a study of interfaces of Kondo lattice layers and normal metals, Peters *et al.*²⁰ showed that such a coupling

transformed the full gap of the Kondo lattice layers into a vanishing soft gap. They also demonstrated the strong influence of the Kondo effect on the density of states of the metallic layer. This proximity effect was further shown to be strongly dependent on the number of non-interacting metallic layers.

Although the proximity effects of strong interactions have been addressed quite rigorously, the effects of disorder have not been considered. Incoherent scattering due to impurities is inevitable in heterogeneous interfaces and therefore the physical effects stemming from disorder could be significant. In fact, in heavy fermion compounds, when magnetic sites are substituted by non-magnetic impurities a substantial reduction of the coherence temperature T_{coh} occurs²⁵. Shimozawa *et al.* studied the effects of Kondo hole disorder on epitaxial thin films of divalent-Yb substituted CeCoIn₅²⁶. It has been shown in Ref 27 that dynamical scattering from Kondo holes can even yield a non-Fermi liquid behavior for bulk systems. Hence, a theoretical study of Kondo hole substituted f -electron interfaces is highly relevant.

In this work, we have explored the spectral dynamics of a single substitutionally disordered Kondo-insulator layer at the boundary of several clean layers of which three types have been considered: (i) non-interacting metals or (ii) band-insulators and (iii) strongly interacting Kondo insulators. We have investigated the penetration of disorder induced impurity scattering into the proximal layers. An interplay of interactions and Kondo hole disorder lead to significant differences in the spectral weight transfer at low frequencies versus the overall spectrum. We argue that, for non particle-hole symmetric systems, the systematic addition of clean interacting layers to the substitutionally disordered interface could lead to a gradual crossover from non-Fermi liquid to Fermi liquid behavior. The paper is organized as follows: The model and methods are described in the next section. The results and discussion follow in Section 3. Our conclusions are presented in the final section.

2. MODEL AND METHOD

The Hamiltonian of a heavy fermion layered system may be constructed through a slight generalization of the standard Periodic Anderson model (PAM) as:

$$\begin{aligned} \mathcal{H} = & - \sum_{ij\alpha\sigma} t_{ij\alpha}^{\parallel} \left(c_{i\alpha\sigma}^{\dagger} c_{j\alpha\sigma} + h.c. \right) \\ & + \sum_{i\alpha\sigma} V_{\alpha} \left(f_{i\alpha\sigma}^{\dagger} c_{i\alpha\sigma} + h.c. \right) \\ & + \sum_{i\alpha\sigma} \left(\epsilon_{c\alpha} c_{i\alpha\sigma}^{\dagger} c_{i\alpha\sigma} + \epsilon_{f\alpha} f_{i\alpha\sigma}^{\dagger} f_{i\alpha\sigma} \right) + \\ & + \sum_{\alpha} U_{\alpha} n_{f\alpha\uparrow} n_{f\alpha\downarrow} - \sum_{i\alpha\sigma} t_{\alpha\alpha+1}^{\perp} \left(c_{i\alpha\sigma}^{\dagger} c_{i\alpha+1\sigma} + h.c. \right), \end{aligned} \quad (1)$$

where, $t_{ij\alpha}^{\parallel}$ represents the in-plane hopping between the conduction band (c -electron) orbitals at sites i and j , in the plane α ; $\epsilon_{c\alpha}$ and $\epsilon_{f\alpha}$ are the onsite energies of the c - and f -electrons, respectively; V_{α} is the hybridization between the heavy f -electrons and the c -electrons in the plane α ; U_{α} is the onsite Coulomb repulsion between two electrons occupying an f orbital in the plane α ; and $t_{\alpha\alpha+1}^{\perp}$ represents the interplane hopping between the delocalized c -orbitals. We explicitly assume here that the f -orbitals being local have negligible overlap between the layers.

The layer Green's functions, $G_{\alpha\beta}^{cc}$ for the c -orbitals, may be obtained through an equation of motion method, applied in real space¹⁹. For an N -layered system, the entire matrix of the c -Green's functions is given by the following expression:

$$\mathbf{G}^{cc}(\omega, \mathbf{k}^{\parallel}) = \begin{pmatrix} \lambda_1 - \epsilon(\mathbf{k}^{\parallel}) & -t_{\perp} & 0 & \dots \\ -t_{\perp} & \lambda_2 - \epsilon(\mathbf{k}^{\parallel}) & -t_{\perp} & \dots \\ 0 & -t_{\perp} & \lambda_3 - \epsilon(\mathbf{k}^{\parallel}) & \dots \\ \vdots & \vdots & \vdots & \vdots \\ 0 & 0 & 0 & \lambda_N - \epsilon(\mathbf{k}^{\parallel}) \end{pmatrix}^{-1}, \quad (2)$$

with $\lambda_{\alpha} = \omega^{+} - \epsilon_{c\alpha} - \Sigma_{c\alpha}$, $\omega^{+} = \omega + i\delta$, and $\mathbf{k}^{\parallel}$ denotes the Bloch vector along the planar direction. Equation (2) assumes the existence of translational invariance along the in-plane direction. The term $\Sigma_{c\alpha}$ is the c -selfenergy arising due to the hybridization with the correlated f -orbitals. The above expression is not restricted to the PAM, and can be used in more general situations, e.g. if the c -orbitals were correlated and thus had an intrinsic selfenergy. The λ_{α} are determined by the Hamiltonian of the α^{th} layer. Note that the band insulator is constructed using a fictitious localized orbital that plays no role except to hybridize with the conduction orbital and create a band gap. For example, λ_{α} is given by $\omega^{+} - \frac{V_{\alpha}^2}{\omega^{+}}$, ω^{+} and $\omega^{+} - V_{\alpha}^2/(\omega^{+} - \epsilon_f - \Sigma_{f\alpha})$ for band-insulators, metals and Kondo insulators respectively, with $\Sigma_{f\alpha}$ being the local f -selfenergy in the α^{th} layer. Within dynamical mean field theory, where the local approximation is valid, an impurity solver is needed to obtain the f -selfenergy. We have employed the local moment approach to solve the effective self consistent impurity problem.

The local c -Green's functions are given by a $\mathbf{k}^{\parallel}$ summation of the $\mathbf{G}^{cc}(\omega, \mathbf{k}^{\parallel})$ matrix. In order to avoid the numerically expensive step of summation over k_x, k_y for each frequency ω , we employ the method used in Ref. 17. If the inverse c -Green's function matrix (in Eq. (2)) is denoted as M' , such that $M' = M - \epsilon(\mathbf{k}^{\parallel})\mathbb{I}$, a similarity transformation may be used to transform the M matrix

into diagonal form, such that,

$$\mathbf{G}^{cc}(\omega) = \mathcal{S} \begin{pmatrix} H[\Gamma_1] & 0 & 0 & \dots \\ 0 & H[\Gamma_2] & 0 & \dots \\ 0 & 0 & H[\Gamma_3] & \dots \\ \vdots & \dots & \vdots & \dots \end{pmatrix} \mathcal{S}^{-1}, \quad (3)$$

where the Hilbert transform, $H[z] = \int_{-\infty}^{\infty} d\epsilon \rho_0(\epsilon)(z - \epsilon)^{-1}$ over $\rho_0(\epsilon)$, the non-interacting planar density of states, represents the result of the $\mathbf{k}^{\parallel}$ summation and $\mathcal{S}$ is the transformation matrix diagonalizing M . The N eigenvalues of M are denoted by Γ_r with $r = 1 \dots N$. The above procedure is valid as long as the band-dispersion is the same for every layer. Within layer-DMFT, each layer is treated as a single-impurity embedded within a non-interacting host. Thus the c -Green's function for the α^{th} layer may be written as

$$G_{\alpha,\alpha}^{cc}(\omega) = \sum_{r=1}^N S_{\alpha r} H[\Gamma_r] (S^{-1})_{r\alpha} \quad (4)$$

$$= \frac{1}{\lambda_{\alpha}(\omega) - \Delta_{\alpha}(\omega)}, \quad (5)$$

where $\lambda_{\alpha}(\omega) = \omega^{+} - \epsilon_{c\alpha} - \Sigma_{c\alpha}$ and $\Delta_{\alpha}(\omega)$ is the host hybridization for the α^{th} PAM layer. Note that Eq. (4) and (5) become the definition of $\Delta_{\alpha}(\omega)$.

An alternative way to approach this problem is through a Feenberg selfenergy approach²⁸. Consider any site on the α^{th} layer. The $\Delta_{\alpha}(\omega)$ for this site may be written as a sum of self avoiding walks on the entire lattice with the lines representing hopping (intralayer given by $-t^{\parallel}$ and interlayer by $t_{\perp}$), and the vertices being the site-excluded Green's functions²⁸. The definition of the hybridization through equations (4) and (5) is a practical route to summing all these diagrams. The local approximation of DMFT implies that the full selfenergy is momentum independent, hence the λ_r will get modified if interactions are included on the r^{th} layer. However, since that is a local change, the diagrams for the $\Delta_{\alpha}(\omega)$ do not change. This implies that the definition of the host hybridization in the presence of interactions remains the same as that for the non-interacting case within DMFT, albeit computed with a new set of λ_r . Including Kondo-hole disorder on the r^{th} layer within the Coherent Potential Approximation (CPA) does not change this definition and is hence tantamount to redefine λ_r in the following way²⁷:

$$\frac{1}{\lambda_r(\omega) - \Delta_r(\omega)} = \frac{1-p}{\gamma_r(\omega) - \Delta_r(\omega)} + \frac{p}{\gamma_{0r}(\omega) - \Delta_r(\omega)}, \quad (6)$$

where $\gamma_r(\omega) = \omega^{+} - \epsilon_{cr} - \Sigma_{cr}$ represents the sites with f -electrons and $\gamma_{0r}(\omega) = \omega^{+} - \epsilon_{cr}$ represents the Kondo hole sites. Thus, for a given set of $\Sigma_{cr}(\omega)$, the $\lambda_r(\omega)$ and $\Delta_r(\omega)$ need to be determined self consistently by

combining equations (4) and (5) with equation (6). A practical computational procedure is the following. Step-1: Guess a set of $\Delta_r(\omega)$ and use them to find λ_r from equation (6). Step-2: Use these λ_r in equations (4) and (5) to find a new set of $\Delta_r(\omega)$. Go back to Step-1 until convergence is achieved. The obtained $\lambda_r(\omega)$ may be used to define a disorder-averaged selfenergy for the r^{th} layer as

$$\Sigma_{cr}^{CPA}(\omega) = \omega^{+} - \epsilon_{cr} - \lambda_r. \quad (7)$$

The self consistent interacting impurity problem is solved here using the local moment approach (LMA). The LMA is a diagrammatic perturbation theory built around the two broken-symmetry, local moment solutions ($\mu = \pm|\mu_0|$) of an unrestricted Hartree-Fock approximation. The diagrams that incorporate dynamics are the transverse spin-flip processes. The symmetry broken at the mean-field level is restored by imposing adiabatic continuity to the non-interacting limit, and this step leads to the emergence of a Kondo scale. The details of the LMA for the single impurity Anderson model and the PAM may be found in references²⁹⁻³². The extension to finite disorder may be found in Ref. 27. We combine LMA, CPA and the inhomogeneous DMFT¹⁹ to explore the effect of disorder and interactions in layered-PAM systems.

3. RESULTS

We have explored the proximity effects of a Kondo hole-disordered heavy fermion layer in thin films, by studying geometries where the substitutionally disordered Kondo insulator is in proximity to several clean interacting or non-interacting layers. Before we delve into results obtained using the numerical implementation of the local moment approach within inhomogeneous DMFT, we present a few general results that are exact within this framework of layered systems.

3.1. Analytical results for a few special cases

Using the equations detailed in Section 2, it is easy to obtain closed-form expressions for the Green's functions in certain simple cases. We present and discuss a few results for a non-interacting layered system, a bilayer and a trilayer system.

1. Non-interacting case

For N -identical layers the matrix on the right hand side of Eq. (2) has the structure of a symmetric tridiagonal Toeplitz matrix³³. The complete eigen-spectrum and corresponding eigenvectors for such a matrix are known

in closed form³³, and hence may be used in combination with Eq. (2) to find the exact Green's functions for the n^{th} layer of a system of N identical non-interacting metallic layers (see also Ref. 34). The density of states at a fixed ω as a function of layer-index becomes:

$$A_n(\omega) = \frac{2}{N+1} \sum_{m=1}^N \sin^2\left(\frac{mn\pi}{N+1}\right) \rho_0\left(\omega + 2t_{\perp} \cos \frac{m\pi}{N+1}\right). \quad (8)$$

With the replacement of ω by $\omega - V^2/\omega$ in the above equation, the result describes N identical non-interacting band-insulators also. $A_n(\omega)$, shown in Figure 1, exhibits

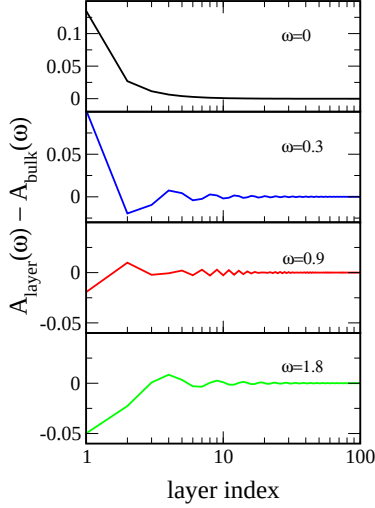


FIG. 1. The change in layer density of states (compared to the bulk) as a function of layer index, for various frequencies. The result was obtained using Equation (8) for a system of 500 layers. The bare density of states for each layer ($\rho_0(\epsilon)$) is chosen to be of semi-elliptic form, $\rho_0(\epsilon) = \sqrt{1 - \epsilon^2/t_{\parallel}^2}/(2\pi t_{\parallel})$.

oscillatory behavior for all ω values except $\omega = 0$ where a monotonic decay is observed. These well-known surface Friedel oscillations arise because the Fermi surface of the infinite metallic system has been perturbed by the presence of terminal surfaces^{10,19}.

2. Bilayer systems: General considerations

For a bilayer system, the Green's functions are given by

$$G_{11}(\omega) = a H[\Gamma_+] + b H[\Gamma_-], \quad (9)$$

$$G_{22}(\omega) = a' H[\Gamma_+] + b' H[\Gamma_-], \quad (10)$$

where

$$\Gamma_{\pm} = \frac{1}{2} \left(\lambda_1 + \lambda_2 \pm \sqrt{(\lambda_1 - \lambda_2)^2 + 4t_{\perp}^2} \right), \quad (11)$$

$$\lambda_r = \omega^+ - \epsilon_c - \Sigma_{cr}(\omega), \quad r = 1, 2,$$

$$a = \frac{\Gamma_+ - \lambda_2}{\Gamma_+ - \Gamma_-} \quad \text{and} \quad b = \frac{\lambda_2 - \Gamma_-}{\Gamma_+ - \Gamma_-}, \quad (12)$$

$$a' = -\frac{\lambda_1 - \Gamma_+}{\Gamma_+ - \Gamma_-} \quad \text{and} \quad b' = \frac{\lambda_1 - \Gamma_-}{\Gamma_+ - \Gamma_-}, \quad (13)$$

and $H[z]$ represents the Hilbert transform with respect to the non-interacting layer density of states. These equations may now be analyzed for a few specific cases.

3. A clean Kondo insulator-metal bilayer system

As a first application of Equations (9) and (10), we consider a Kondo-insulator-metal interface. The paramagnetic Kondo insulator is just a renormalized band-insulator, hence in the particle-hole symmetric limit, $\epsilon_c = 0$ and $\Sigma_c(\omega) = V^2/(\omega^+ - \epsilon_f - \Sigma_f)$. In the low frequency limit, the Fermi-liquid form of the f -selfenergy may be used to get $\Sigma_c \xrightarrow{\omega \rightarrow 0} ZV^2/\omega^+$, where $Z = (1 - \partial\Sigma_f/\partial\omega)^{-1}$ is the f -electron quasiparticle weight. Thus, $\lambda_1 = \omega^+ - ZV^2/\omega^+$ for the Kondo insulator and $\lambda_2 = \omega^+$ for the non-interacting metal. Given these, the c-spectral functions $A_l(\omega) = -\text{Im}G_{ii}^c(\omega)/\pi$ for the Kondo insulator ($i = 1, l = KI$) and metal ($i = 2, l = M$) layers in the low frequency limit are given by,

$$A_{KI}(\omega) \xrightarrow{\omega \rightarrow 0} \left(\frac{\omega t_{\perp}}{ZV^2} \right)^2 \rho_0 \left(\omega \left[1 + \frac{t_{\perp}^2}{ZV^2} \right] \right) + \left(1 - \left(\frac{\omega t_{\perp}}{ZV^2} \right)^2 \right) \rho_0 \left(\omega \left[1 - \frac{t_{\perp}^2}{ZV^2} \right] - \frac{ZV^2}{\omega} \right), \quad (14)$$

$$A_M(\omega) \xrightarrow{\omega \rightarrow 0} \left(1 - \left(\frac{\omega t_{\perp}}{ZV^2} \right)^2 \right) \rho_0 \left(\omega \left[1 + \frac{t_{\perp}^2}{ZV^2} \right] \right) + \left(\frac{\omega t_{\perp}}{ZV^2} \right)^2 \rho_0 \left(\omega \left[1 - \frac{t_{\perp}^2}{ZV^2} \right] - \frac{ZV^2}{\omega} \right). \quad (15)$$

From the above expressions, we see that the presence of interlayer coupling ($t_{\perp} > 0$) leads to a linear mixing of the Kondo-insulator and metallic layer spectra in all layers. In $A_{KI}(\omega)$, the first term contributes a quadratically vanishing spectral weight into the hybridization gap, while the second-term leads to the usual gapped spectrum of the Kondo insulator. In $A_M(\omega)$, the first term implies that the spectrum of the non-interacting metal is strongly renormalized by the proximity to the Kondo insulator, and a Kondo resonance like feature must emerge in the vicinity of the Fermi level. The second term is gapped at the Fermi level, but should

lead to a step like feature at $\omega \sim ZV^2$. Thus, the metallic states tunnel into the gap of the Kondo insulator giving rise to a quadratically vanishing gap, while the strongly correlated Kondo insulator tunnel into the non-interacting metal leading to strong renormalization of the non-interacting spectrum. In the Kondo insulator, the f -electron spectrum is related to the c -electron spectrum through $A_{KI}^f(\omega) = (Z^2 V^2 / \omega^2) A_{KI}(\omega)$ in the limit $\omega \rightarrow 0$. Due to the tunneling of the metallic states into the Kondo insulator, the f -spectrum thus becomes gapless. These proximity effects are quite general and only assume a linear expansion in frequency of the real part of the f -selfenergy. Similar results have been observed numerically in a recent study on a single Kondo insulator embedded in a three-dimensional non-interacting metallic host²⁰ and in a theoretical analysis of the surface density of states of heavy fermion materials²⁴. This physical scenario of "Kondo Proximity Effect" was used to qualitatively explain the experimental surface spectra of CeCoIn₅ reported by Aynajian *et al.*³⁵.

4. A clean Kondo insulator-band insulator bilayer system

Next, we consider a Kondo-insulator-band-insulator interface. For the band insulator, $\lambda_2 = \omega^+ - V^2/\omega^+$. Thus, the spectral functions are again given by a linear mixing of the Kondo and the band insulator spectra. A low frequency analysis similar to the one carried out above for the Kondo insulator-metal system leads to the following. The gap in the Kondo insulator is well known to be substantially reduced compared to the band insulator due to the exponentially small quasiparticle weight factor Z arising in the strong coupling limit. Thus, from our analysis, we see that the Kondo insulator spectrum close to the Fermi level remains almost unchanged. However, in the frequency region where the band insulator had a gap, but the Kondo insulator had states, a quadratically vanishing spectral weight tunnels in from the Kondo insulator layer into the band insulator.

5. A dirty Kondo insulator-metal bilayer system

In this sub-section, we consider, in detail, a substitutionally disordered-Kondo-insulator interfaced with a non-interacting metal. The random substitution of f -sites in the Kondo insulator-layer leads to Kondo hole disorder, which is known to lead to an impurity band at the Fermi level^{36,37}. Specifically, λ_1 becomes complex because of the static contribution to the selfenergy from scattering by impurities²⁷. Thus $\lambda_1 = \omega^+ / Z + i\Gamma_0$, where Z is the local f -electron quasiparticle weight and $\Gamma_0 = -\text{Im}\Sigma_c^{CPA}(0)$ is the scattering rate at the Fermi level. In a previous paper²⁷, we showed that Σ_c^{CPA} may be related to Σ_c through a cubic equation if $\rho_0(\epsilon)$ has a semi-elliptic form that corresponds to an infinite-dimensional Bethe lattice. This equation, if used for a

single isolated Kondo insulator, yields that

$$\Sigma_c^{CPA}(0) = -it_{||} \frac{1-p}{2\sqrt{p}}, \quad (16)$$

Thus, at the Fermi level, the conduction electrons acquire a selfenergy that is non-analytic in the concentration of Kondo holes, p . It was also shown in Ref. 37 that the f electron selfenergy acquires a $1/\sqrt{p}$ dependence when $p \rightarrow 0$. However, in the presence of interlayer coupling, Γ_0 becomes a complicated function of $t_{\perp}$ and $t_{||}$ and we have not been able to find a simple closed form expression like Equation (16) for the bilayer case. Nevertheless, numerical calculations lead us to the conclusion that Γ_0 does retain the same form as the isolated layer case.

Our natural focus is on the strong coupling regime of the Kondo insulator, where the quasiparticle weight becomes exponentially small, i.e $Z \rightarrow 0$. In such a situation, and with $\lambda_1 = \omega^+ / Z + i\Gamma_0$ and $\lambda_2 = \omega^+$, the values of $\Gamma_{\pm}$ in Equation (11) may be simplified to

$$\Gamma_{\pm} \xrightarrow{Z \rightarrow 0} \frac{1}{2} \left(\lambda_1 \pm \sqrt{\lambda_1^2 + 4t_{\perp}^2} \right). \quad (17)$$

The coefficients of the Hilbert transforms in equation (9) and (10) are given by

$$\begin{aligned} a &\rightarrow \frac{\Gamma_+}{\sqrt{\lambda_1^2 + 4t_{\perp}^2}} & b &\rightarrow \frac{-\Gamma_-}{\sqrt{\lambda_1^2 + 4t_{\perp}^2}} \\ a' &= b \text{ and } b' = a. \end{aligned} \quad (18)$$

These equations are quite easy to analyze at the Fermi level ($\omega = 0$). In fact, the results from this analysis do not assume strong coupling, because if we substitute $\omega = 0$ in the above expressions, the quasiparticle weight does not appear in them. Hence the following results are valid for any coupling strength. At the Fermi level, the eigenvalues are given by

$$\Gamma_{\pm} = \frac{i}{2} \left(\Gamma_0 \pm \sqrt{\Gamma_0^2 - 4t_{\perp}^2} \right). \quad (19)$$

Γ_0 is a monotonically decreasing function of the Kondo hole concentration (see equation (16)) and hence in the dilute limit ($p \rightarrow 0$), the eigenvalues will be purely imaginary; with increasing p , $\Gamma_{\pm}$ become degenerate at $\Gamma_0 = 2t_{\perp}$, which translates to a specific concentration, p_d . In general, p_d is a complicated function of Γ_0 . However, we have numerically verified that when the ratio $t_{\perp}/t_{||} \ll 1$, Eq. (16) can be used as an estimate of p_d for multi-layer systems. For such a regime $p_d = (\sqrt{1 + (2t_{\perp}/t_{||})^2} - 2t_{\perp}/t_{||})^2$. For $p > p_d$, the two eigenvalues have the same imaginary part but differ in the real part. It turns out that the density of states at the Fermi level can be easily obtained in two limits: the dilute limit ($p \rightarrow 0$) and the degenerate limit ($\Gamma_0 = 2t_{\perp}$ or $p = p_d$). We proceed to obtain these.

In the dilute limit, $\Gamma_0 \gg t_{||}, t_{\perp}$, so $\Gamma_{\pm} \rightarrow i(\Gamma_0 - t_{\perp}^2/\Gamma_0)$

and $\Gamma_- \rightarrow it_\perp^2/\Gamma_0$. For purely imaginary arguments ($z = i\eta$), the Hilbert transform with respect to a semi-elliptic density of states may be written in closed form as

$$\mathcal{H}(i\eta) = \int \frac{\rho_0(\epsilon)}{i\eta - \epsilon} = -\frac{2i}{t_\parallel} \left[\sqrt{1 + \bar{\eta}^2} - \bar{\eta} \right], \quad (20)$$

where $\bar{\eta} = \eta/t_\parallel$. So the Hilbert transform is also purely imaginary, which can be expected in the particle-hole symmetric limit. Using the above Hilbert transform result and the simplification of the eigenvalues in the dilute limit, the density of states of the Kondo insulating layer and the non-interacting metallic layer are given by (to $\mathcal{O}(1/\Gamma_0^2)$)

$$A_{KI}(\omega = 0) \xrightarrow{p \rightarrow 0} \frac{1}{\pi\Gamma_0} \left[1 - \frac{2t_\perp^2}{\Gamma_0 t_\parallel} \right] \quad (21)$$

$$A_M(\omega = 0) \xrightarrow{p \rightarrow 0} \frac{2}{\pi t_\parallel} \left[1 - \frac{t_\perp^2}{\Gamma_0 t_\parallel} + \frac{t_\perp^2}{\Gamma_0^2} \right]. \quad (22)$$

Note that in all the equations above and below, $A_{KI}(\omega)$ denotes the c -electron spectral function of the Kondo insulator. The above equations reveal the proximity effect of disorder on the two layers. In the absence of inter-layer tunneling, the impurity band in the Kondo insulator grows as $\sqrt{p}$ with increasing Kondo hole substitution (since $\Gamma_0 \sim 1/\sqrt{p}$ in the dilute limit); and the metallic layer has a fixed density of states ($= 2/(\pi t_\parallel)$) at $\omega = 0$. When $t_\perp$ is turned on, the impurities introduced in the Kondo insulating layer affect the density of states of the non-interacting clean metallic layer, and the relative change in the density of states with respect to the isolated layers ($t_\perp = 0$) case is $\sim \sqrt{p}$ for both layers.

In the degenerate limit, $\Gamma_0 = 2t_\perp$, the eigenvalues are degenerate, and Eq. (9) and (10) cannot be used. We revert back to the basic equation (3) and after a bit of algebra, obtain the density of states of the two layers as

$$A_{KI}(\omega = 0) \xrightarrow{p=p_d} \frac{2}{\pi t_\parallel} \frac{\left(t_r - \sqrt{1 + t_r^2} \right)^2}{\sqrt{1 + t_r^2}}, \quad (23)$$

$$A_M(\omega = 0) \xrightarrow{p=p_d} \frac{2}{\pi t_\parallel} \frac{1}{\sqrt{1 + t_r^2}}, \quad (24)$$

where $t_r = t_\perp/t_\parallel$ is the ratio of the inter-layer to intra-layer hopping. We have seen that the metallic layer acquires a Kondo resonance at the Fermi level due to the proximity to the Kondo insulator. Since in the concentrated limit ($p \rightarrow 1$), the entire system simply becomes a non-interacting metallic bilayer, the density of states must approach the value of $\rho_0(t_\perp)$. It can also be shown that, the $A_M(\omega = 0) > \rho_0(t_\perp)$. This implies that both the metallic layer and the Kondo insulating layer experience a monotonic change in the density of states with increasing Kondo hole concentration; the Kondo insulating layer steadily transforming into a single-impurity system.

6. Symmetric tri-layer systems

Another class of systems, for which closed form expressions may be readily obtained is a set of three layers in which the outer two layers are identical in all respects while the middle layer is different. The c -Green's function for such a system (denoted by 1-2-3) is given by

$$G_{11}(\omega) = G_{33}(\omega) = \frac{1}{2} H[\lambda_1] - t_\perp^2 (a H[\Gamma_+] + b H[\Gamma_-]), \quad (25)$$

$$G_{22}(\omega) = a' H[\Gamma_+] + b' H[\Gamma_-], \quad (26)$$

$$\text{where} \quad (27)$$

$$\Gamma_\pm = \frac{1}{2} \left(\lambda_1 + \lambda_2 \pm \sqrt{(\lambda_1 - \lambda_2)^2 + 8t_\perp^2} \right),$$

$$\lambda_r = \omega^+ - \epsilon_c - \Sigma_{cr}(\omega),$$

$$a = \frac{1}{(\lambda_1 - \Gamma_+)(\Gamma_+ - \Gamma_-)} \text{ and}$$

$$b = \frac{-1}{(\lambda_1 - \Gamma_-)(\Gamma_+ - \Gamma_-)},$$

$$a' = -\frac{\lambda_1 - \Gamma_+}{\Gamma_+ - \Gamma_-} \text{ and } b' = \frac{\lambda_1 - \Gamma_-}{\Gamma_+ - \Gamma_-}. \quad (28)$$

For the trilayer system, if the layers are uncoupled ($t_\perp = 0$) then the Green's functions should be simply given by $G_{ii}(\omega) = H[\lambda_i]$. In order to approach the uncoupled layers limit, in the equations above, the limit of $t_\perp \rightarrow 0$ must be taken with care. We have investigated the symmetric tri-layer system in several situations, that are similar to the ones discussed for the bilayer system. One of these is a Kondo insulator, which could be clean or substitutionally Kondo hole disordered, sandwiched between two metallic or band-insulating layers. The conclusions reached in such cases were found to be qualitatively very similar to those in the bilayer systems, hence we now proceed to larger systems and investigate the penetration of disorder into several clean, non-interacting or interacting layers.

In the next sub-section, we discuss full numerical solutions using the formalism described in Section 2.

3.2. Numerical results

It is evident that the spectral changes in the c - and f -electron Green's functions are a combined effect of the three physical parameters in the problem, namely: (i) interlayer-hopping, $t_\perp$, (ii) interaction, U , and (iii) Kondo hole concentration (p). In order to disentangle the sole effect of disorder from the results, we first discuss briefly the non-interacting and clean layered systems. Then, we add interactions and note the combined effect of inter layer coupling and interactions. Finally, we add disorder and by comparing the obtained spectra to those of the non-disordered case, we isolate the

proximity effects of disorder, which represents the main objective of this paper. We study three different cases, with a single substitutionally disordered Kondo insulator layer next to (a) several band-insulator, (b) several uncorrelated metal and (c) several clean Kondo insulator layers. These three cases will be referred to as disordered Kondo insulator-band insulator, disordered Kondo insulator-metal and disordered Kondo insulator-Kondo insulator, respectively. A schematic of the geometries is shown in Fig. 2. The number of clean layers has been varied from 1 to 11. The clean metals are

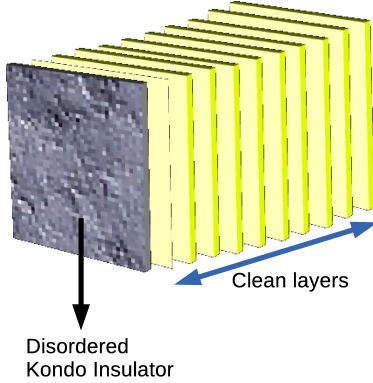


FIG. 2. Schematic of the geometry considered in this work. While the boundary layer is chosen to be a dirty Kondo insulator, the proximal layers are clean. Three distinct possibilities for these clean layers have been investigated, namely band-insulators, metals or Kondo insulators.

just $U = 0$ layers with a simple tight-binding Hamiltonian. In the disordered Kondo insulator-Kondo insulator case, all the Kondo-insulating layers including the disordered layer have the same U and V . All of the numerical results have been obtained by using a semi-elliptic bare density of states for each layer, namely, $\rho_0(\epsilon) = \sqrt{1 - \epsilon^2/t_{||}^2}/(2\pi t_{||})$, with $t_{||} = 1$ as the unit of energy. We begin this section by considering the effects of $t_{\perp}$ only, in a clean, non-interacting, f - conduction-electron system, interfaced with several non-interacting metals or several other non-interacting f - conduction-electron systems.

1. Effects of inter-layer hopping: $t_{\perp} \neq 0$, $U = 0$, $p = 0$

The exact solution of a system of N -identical layers discussed in the previous section shows that Friedel oscillations are induced in the density of states when the bulk Fermi surface is perturbed. For an infinite layer system, the inter-layer hopping would simply create an energy band in the direction perpendicular to the planes. The introduction of a terminal surface into such a bulk system gives rise to surface Friedel oscillations. For finite layer-systems, the surface Friedel oscillations would be very

pronounced and would naturally depend on the nature of the terminal/boundary layer. For non-identical layers, exact solutions are not available, however, the numerical solution may be obtained almost trivially. In Fig. 3, the

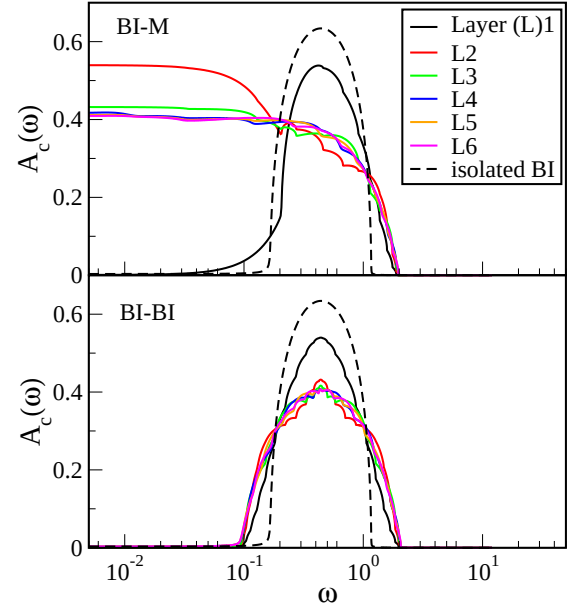


FIG. 3. Spectral density of the c electrons in the presence of non-zero interlayer coupling for a single band insulator layer (L1) at one end of a 11-layer (L2-L12) metallic system (top panel) and a single band insulator at one end of a 11-layer band insulating system (bottom panel). The model parameters are $t_{\perp} = 0.5$, $U = 0$, $V = 0.44$. Note that only $\omega > 0$ is displayed on a logarithmic axis. For comparison, the spectrum of an isolated band insulator layer is shown as a dashed line.

layer-resolved c -spectra for a single band insulator coupled to 11 metallic layers is shown. Since the entire system is particle-hole symmetric, we choose to display only the $\omega > 0$ spectrum on a logarithmic axis. The spectrum for an isolated band insulator layer is shown as a dashed line in both panels. From the top panel of figure 3, we observe that the presence of $t_{\perp}$ between a metallic layer next to a band insulator leads to the tunneling of metallic states into the otherwise large hybridization gap of the band insulator. We had predicted earlier, through equations (14) and (15), that the presence of $t_{\perp}$ leads to a quadratic rounding off of the band insulator band edge, which is evident when compared with the hard band edge of the isolated layer's hybridization gap (dashed line). The multiple Friedel oscillations due to a non-zero $t_{\perp}$ are also visible in Fig. 3. Although equations (14) and (15) were exact for a bilayer system, the layer resolved spectra follow the same qualitative changes in this multi-layered system. These oscillations naturally attenuate sharply in the layers that lie far from the boundaries. However, for all the finite-layer systems that we have studied, these oscillations are present. Nevertheless, as Freericks *et al.* discussed in Ref. 19, and also found by us, the amplitude

of these oscillations in the surface layers become frozen-in once the system becomes large ($\gtrsim 10$ layers in practice).

Next, we explore the combined effect of inter-layer coupling and interactions.

2. *Combined effect of inter-layer hopping and interactions:*
 $t_{\perp} \neq 0, U \neq 0, p = 0$

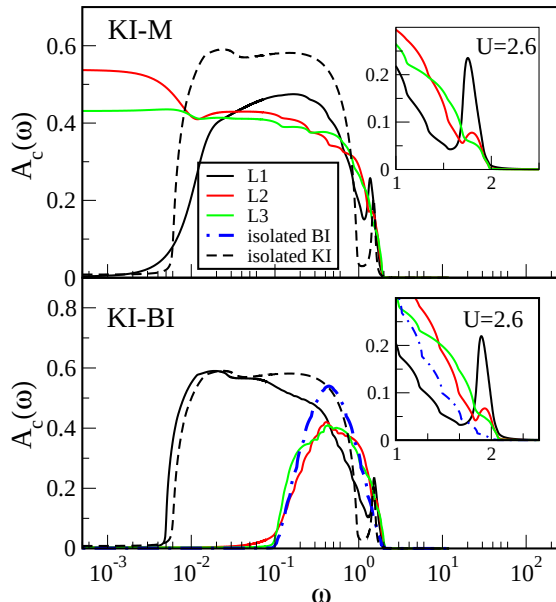


FIG. 4. Layer resolved spectral function for the c electrons due to non-zero interlayer hopping and interactions. A single Kondo insulator layer (L1) is coupled to a 11 layer metallic system (top panel) and a 11 layer band insulating system (bottom panel). The spectra for the nearest (L2) and second nearest (L3) metallic (top panel) and the band insulator (bottom panel) is shown. For both panels inter-layer hopping $t_{\perp} = 0.5$, and $c - f$ hybridization is set to $V = 0.44$ for both the Kondo insulators and the band insulators, Coulomb repulsion in the Kondo insulating layer $U = 1.7$ in the main panels and $U = 2.6$ in both insets. For comparison, the c -DOS of an isolated Kondo insulator and an isolated band insulator is also shown as (black) dashed (top and bottom panel) and (blue) dashed-dotted lines (bottom panel), respectively. The insets show the Hubbard bands that emerge as a result of their proximity to the coupled Kondo insulator. This effect is visibly detectable only until the second nearest neighbor layer.

In the context of bulk systems, the presence of interactions on the f -orbitals in an otherwise simple band insulator leads to a strongly renormalized hybridization gap and hence a Kondo insulator. The proximity of a strongly interacting Kondo insulator to a non-interacting layer, either a band insulator or a metal, is an interesting problem. Our analysis in previous section showed that the proximity of a band insulator to a Kondo insulator layer results in a rounding off of the hybridization band edge of the band insulator, while the Kondo

insulator layer remains almost unaffected. If the band insulator is replaced by a metal, then we saw that the metallic states tunnel into the Kondo insulator, while strong correlations in the Kondo insulator tunnel into the non-interacting metal and give rise to a Kondo resonance like feature. This is consistent with the numerical renormalization group results of Peters *et al.* on Kondo superlattices²⁰. Our results, although derived for bilayer (Kondo insulator-band insulator and Kondo insulator-metal) systems, remain robust even when the number of band insulator or metal layers is increased. For example, in Fig. 4 we show the layer-resolved c -spectra for a single Kondo insulator and 11 metallic layer system (top panel) and a single Kondo insulator and 11 band insulator layer system (bottom panel). In this bottom panel, due to the presence of finite density of states in the proximal Kondo insulator, we see that the c -spectra of the second neighboring band insulator layer acquires a quadratic rounding off around the band edge. The farther band insulator layers are however inert to these effects.

The top panel of Fig. 4 shows that, for a metallic layer adjacent to a Kondo insulator, the proximity effect results in a Kondo-like resonance at the Fermi level of the otherwise non-interacting metal. This is the Kondo proximity effect discussed in Ref. 20. Proximity to a strongly interacting Kondo insulator induces changes not only at low energies such as the Kondo scale, but also at high energies such as Hubbard bands. The adjacent non-interacting band-insulating or metallic layers also acquire minute Hubbard bands indicating the tunneling of electron correlations into the non-interacting layers. Similar effects occur even in bulk heavy fermions, modeled by the periodic Anderson model, where although the U is present only for f -electrons, the mixing between c - and f -electrons through the hybridization produces Hubbard bands in the spectrum of the conduction band electrons. Whether the single Kondo insulator is coupled to band-insulating or metallic layers, these high energy proximity effects are the same, which is evident from the insets of Fig. 4. Now we proceed to explore the spectral modifications induced in the layer resolved spectra when we introduce Kondo holes in the boundary Kondo insulator layer.

3. *Effects of Kondo hole disorder in the boundary layer*

The effects of Kondo-hole disorder in the bulk PAM have been extensively investigated^{25,27,36,37}. It is well known that there is a crossover from coherent lattice behavior to incoherent single-impurity behavior as the disorder p changes from zero to one^{25,27}. Such a crossover is reflected in all physical quantities, including resistivity, thermopower and density of states. For layered systems, the range and extent of disorder effects may be quantified through a measurement of integrated spectral weight difference in a given frequency interval $|\omega| \leq \lambda$. We define $\chi_{\nu}(p, p_0; \alpha; \lambda)$, as the spectral weight difference of the α^{th}

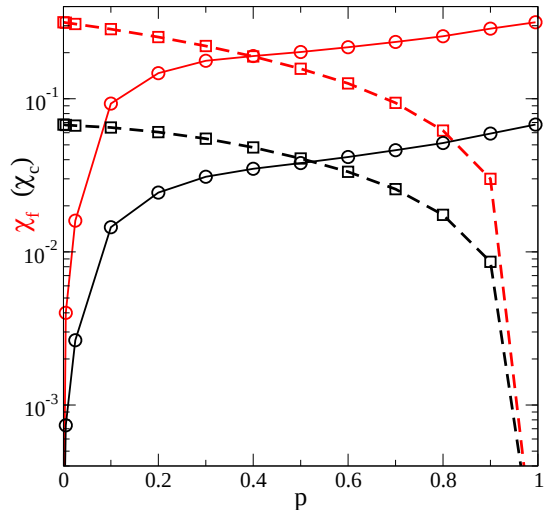


FIG. 5. The spectral weight difference between the disordered and the clean c - and f -spectral functions for a single PAM layer as a function of Kondo hole concentration p . Red lines and symbols correspond to the f spectra function, while black lines and symbols correspond to the c -spectral functions. The solid lines with circles represent the spectral weight difference with respect to the $p = 0$ (clean) case, the dashed lines with squares correspond to the comparison with the $p \rightarrow 1$ limit. The parameters used are $U = 1.7$, $V = 0.44$, and $t_{\perp} = 0.0$.

layer, computed through

$$\chi_{\nu}(p; p_0; \alpha; \lambda) = \int_{-\lambda}^{\lambda} d\omega |A(p; \{U_{\beta}\}; \alpha; \omega) - A(p_0; \{U_{\beta}\}; \alpha; \omega)| \quad (29)$$

for a set of fixed interaction strengths $\{U_{\alpha}\}$. Here $\nu = c/f$ and $A(p; \{U_{\beta}\}; \alpha; \omega) = -\text{Im}G_{\alpha}(p; \{U_{\beta}\}; \omega)/\pi$ is the spectral function of the α^{th} layer's when the Kondo hole concentration is p . Physically, this quantity represents the extent to which the layer density of states changes when disorder goes from p_0 to p or vice-versa when all other parameters are fixed. We have employed $n_c = 1$ and $n_f = 1$ for an isolated Kondo insulator layer. With random dilution of f -sites, which introduces Kondo hole disorder, an impurity band is expected to form at the Fermi level. The spectral weight difference of an isolated disordered Kondo insulator layer with respect to the clean ($p_0 = 0$) and single-impurity ($p_0 \rightarrow 1^-$) limits as a function of Kondo hole concentration p is shown in Fig. 5 (with the cutoff $\lambda \rightarrow \infty$). The spectral weight difference between the disordered and the clean case integrated over all frequencies (shown in Fig. 5 as solid lines with circles) is seen to rise rapidly as a function of increasing p and roughly saturate at the concentration of $p \sim 0.5$. The spectral weight difference at $p \sim 0.5$ is large when compared with either clean case ($p = 0$) or the $p \rightarrow 1^-$ single-impurity case (shown in Fig. 5 as dashed lines with squares). Hence we choose a fixed disorder

$p = 0.5$ on the boundary layer in all of our subsequent discussion, unless otherwise mentioned. The rest of the layers are chosen to be clean.

With the experimental realizations of $\text{CeIn}_3/\text{LaIn}_3$ superlattices²³ and thin films of non-magnetic Yb substituted into CeCoIn_5 ²⁶, the possibility of having an interface between a Kondo hole disordered layer and a clean layer cannot be ignored. We focus on the following questions: How does the random dilution of f -electrons in a single Kondo insulator boundary layer (see schematic Fig. 2) affect the dynamics of the electrons in the adjoining clean layers? How far do the disorder effects penetrate? And does this range get enhanced or suppressed by the presence of interactions?

In order to answer these questions, we therefore investigate the interface of a single disordered Kondo insulator and several clean layers that could be non-interacting metals or band-insulators or strongly interacting Kondo insulators. We start our discussion with a system of 12 layers where the boundary layer is a disordered Kondo insulator and the rest of the layers are non-interacting metals. We refer to this as a disordered Kondo insulator-metal system. The proximity of a clean Kondo insulator to a metal leads to (i) a quadratic band bending at the Kondo hybridization band edge of the Kondo insulator layer and (ii) appearance of a Kondo resonance and a strongly renormalized low energy spectra induced by the "Kondo proximity effect". This has already been discussed earlier for a bilayer Kondo insulator-metal interface. In the presence of disorder, it is well known that Kondo holes introduce an impurity band in the center of the Kondo hybridization gap³⁶. This impurity band then fills up the gap with increasing disorder concentration, leading to a continuum of metallic states spanning the entire gap. This observation holds here too as seen in the panel (i) of Fig. 6. This phenomenon due to Kondo holes manifests itself in both the CPA averaged c -electron spectra and the local (impurity) f -electron spectra of the disordered Kondo insulator (not shown here). Additionally, the Hubbard bands get depleted due to the presence of Kondo holes. The important aspect however, is that these disorder effects do not just remain confined to the disordered layer but also penetrate into the neighboring clean layers depicted in the lower panels of figure 6. Disorder in fact destroys the proximity effects of interactions. The Kondo resonance in the adjoining metallic layer at zero disorder appreciably reduces in intensity when the Kondo hole concentration, p is 0.5 and tends to disappear as p increases. This is more clearly visible from figure 7. The low energy spectra of the farther neighbors also acquire visible low energy spectral changes that evolve with change in disorder concentration, tending to crossover to the noninteracting limit of a clean metal/metal interface, as seen from figure 7. The tiny Hubbard bands in the non-interacting layers also disappear with increasing disorder. This can be expected qualitatively because introducing Kondo holes implies that sites with f -orbitals in the boundary layer are randomly being replaced by non-

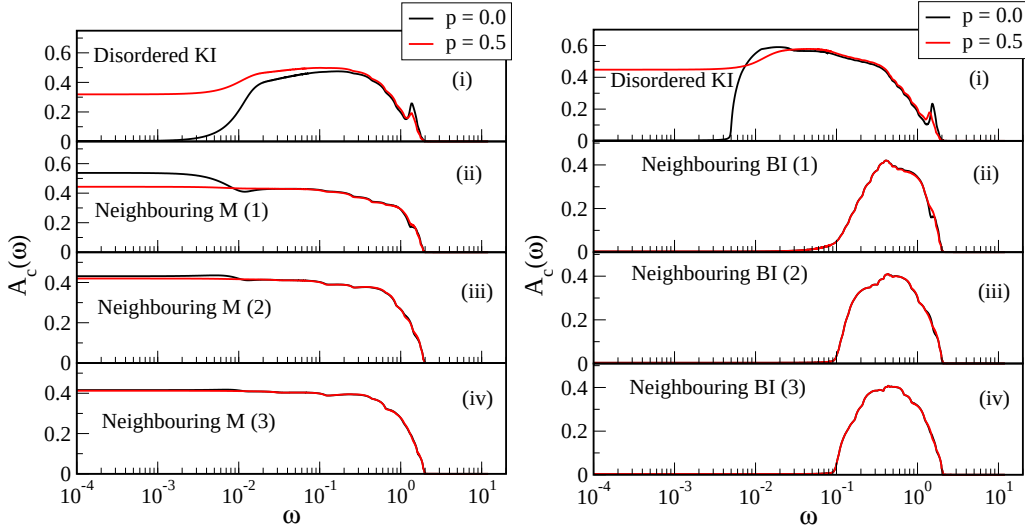


FIG. 6. The c -electron spectra of the respective layers as denoted in the panels for a single disordered Kondo insulator interfaced with a 11-layer metallic (M) (left panel) or band insulating (BI) (right panel) system for a clean ($p = 0$) (solid black) and a disordered ($p = 0.5$) Kondo insulating (KI) layer (solid red). For the disordered Kondo insulator this represents the CPA average of $-\Im G_{\text{CPA}}/\pi$. The model parameters are $t_{\perp} = 0.5$, $V = 0.44$, $U = 1.7$.

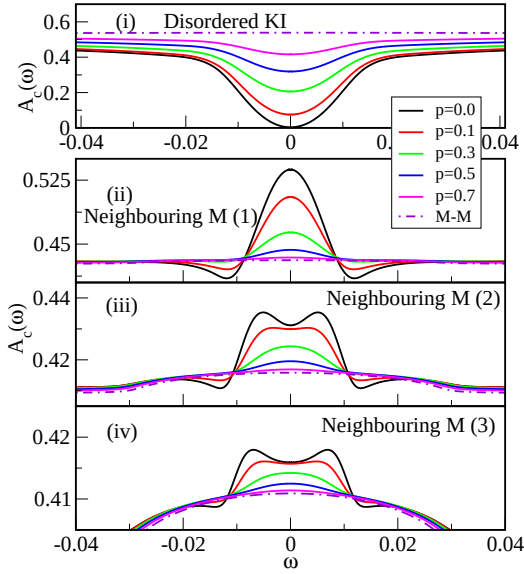


FIG. 7. Spectral evolution at low energies for the disordered Kondo insulator (panel(i)) and the proximal clean metals (panel(ii)-(iv)). A system of a single disordered Kondo insulator and 11 clean metallic layers is used. The respective layer-resolved metallic spectra corresponding to a 12 layer metal-metal (M-M) system is also shown for comparison. The model parameters are the same as used in Fig. 6

interacting sites, hence the effects of interactions should get mitigated not only in the layer but also in the adjoining layers.

The penetration of Kondo holes into proximal band insulating layers is however different (than the proximity to

metals discussed above). The exponentially larger non-interacting hybridization gap of the proximal band insulators prohibit electrons from tunneling into the insulating gap. Thus, disorder induced spectral changes in proximal band insulators remain confined to the band edges and the high energy Hubbard bands. To this end, we refer back to our discussion on the Kondo insulator/band insulator bilayer interface in section 3.3.1.4. There we realized that, around the band edges of the proximal band insulator, where the Kondo insulator has available states, a quadratic band bending would occur owing to the interlayer coupling. If the clean layers are also interacting Kondo-insulators, the proximity effects of disorder span over all frequency scales, from the universal, hybridization gap scale to the non-universal, Hubbard bands. This shall be discussed now.

The boundary layer metallic states introduced by Kondo hole disorder now tunnel into the adjoining Kondo insulator, causing the quadratic bending of the gap in the adjacent layer (see figure 8). This tunneling effect does propagate into the further layers, but is attenuated by the ω^2 factor and is hence too small to be observed. The mechanism of penetration of the Kondo hole disorder induced metallic states from the disordered Kondo insulator to the coupled clean Kondo insulator is thus physically very similar to that of a clean metal interfaced with a clean Kondo insulator (Eqs (14), (15)).

In the disordered Kondo insulator layer, spectral weight transfer occurs across all scales. It is well known that Kondo hole substitution results in a coherent lattice to an incoherent single-impurity crossover. This manifests in the transfer of weight from high energy Hubbard bands to the Kondo resonance. Concomitantly, the hybridization experienced by the interacting sites

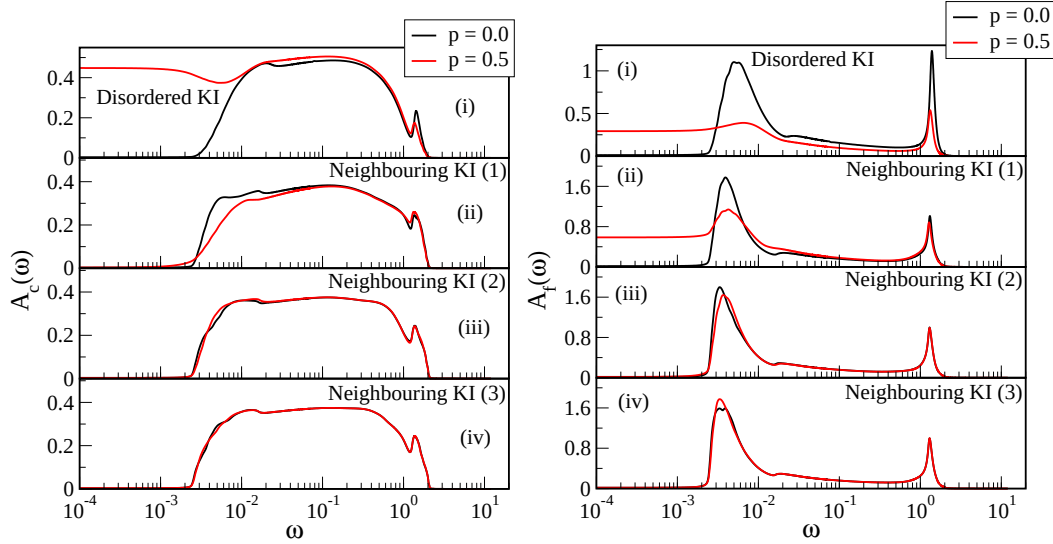


FIG. 8. (Left panel): The layer resolved c -electron spectra of a single disordered Kondo insulator coupled to 11 clean Kondo insulating (KI) layers. The respective layers are denoted in the panels; (right panel): The same for the CPA averaged f -electrons of the disordered Kondo insulator and the interacting f -electrons of the clean Kondo insulators. The parameters used are $t_{\perp} = 0.5$, $V = 0.44$, $U = 1.7$

in the boundary layer crosses over to a featureless non-interacting lineshape. The adjacent layers get strongly affected by these changes and the spectral weight transfer occurs across all energy scales in the nearest neighbor Kondo insulator as well. The Hubbard bands in the second layer too acquire an explicit Kondo hole induced depletion. Although there exists no explicit interlayer f - c hybridization the f -electrons in the clean layers get strongly influenced by the presence of Kondo holes in its adjacent layer. This is because the f - e^- s of the proximal clean layers see a self consistently determined layer dependent host hybridization function, $S(\omega)$, as can be seen from Eq(5). We now quantify the spectral weight transfers focusing on the role of interactions in the proximity effects of disorder.

As explained earlier, the spectral weight difference between the spectra, with and without disorder, integrated in a given frequency interval, represents one measure of the proximity effect of disorder. We have chosen two frequency intervals: (i) a ‘low’ frequency interval defined by $|\omega| \leq \Omega_{BI}$, where $\Omega_{BI} = \frac{1}{2} \left(-t_{||} + \sqrt{t_{||}^2 + 4V^2} \right)$, represents the hybridization gap edge of an isolated band insulator and (ii) the entire frequency range. This classification into low frequencies and all frequencies is done to emphasize that the low frequency spectral changes could be tiny ($\sim \omega_L \rho_0(0)$, which is exponentially small in strong coupling) but affect low temperature properties, especially transport, in a major way. The spectral changes over *all* frequencies will show up in photoemission and optical properties measurements, and hence are important from a different perspective. Since the Kondo holes are introduced only in the boundary layer, the spectral weight transfers would be maximal there. Moving away

from the disordered Kondo insulator layer, the changes in the spectra due to the boundary layer disorder must decrease. Indeed, this expectation is borne out, as seen in figure 9. The spectral weight difference defined in equation (29) decreases sharply with distance from the disordered Kondo insulator layer for all the three cases considered (interfacing the disordered Kondo insulator with either 11 metals, or 11 band/Kondo insulators) thus far. These spectral weight changes quantify the proximity effects of disorder, in the absence or presence of interactions. The fits of the spectral weight difference (dot-dashed lines in figure. 9) show that the proximity effects decay algebraically with increasing distance from the boundary layer. Such a decay profile indicates that changes made in the boundary layer can penetrate quite deep into the system.

Apart from the overall decay profile, there are subtle aspects of the spectral weight difference that we highlight now. The main panel in figure 9 shows the spectral weight difference computed over all frequency scales ($\lambda \rightarrow \infty$). The spectral changes in the non-interacting as well as interacting layers are seen to be similar up to the third layer, beyond which the Kondo insulating layers are far less affected than the non-interacting metallic or band-insulating layers. However, the low frequency spectral weight difference ($\lambda = \Omega_{BI}$), shown in the inset, presents an entirely different picture. The band-insulators are seen to be least affected, since the spectral weight difference drops rapidly by over a decade even for the layer adjacent to the disordered Kondo insulator boundary layer. In contrast, the metallic and Kondo-insulating layers experience similar levels of spectral changes due to the disorder in the boundary layer. Thus, when viewed over all scales, interactions indeed

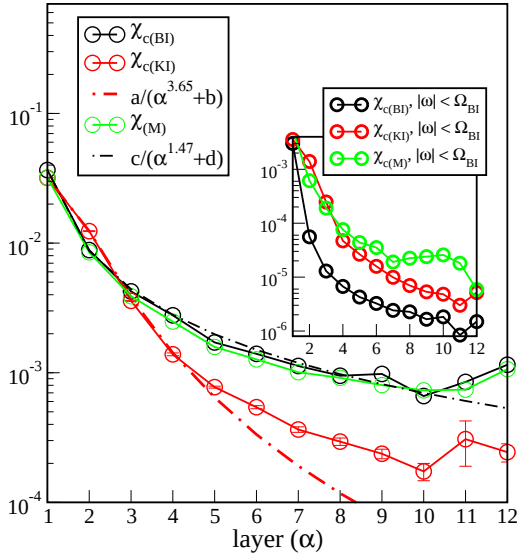


FIG. 9. The integrated spectral weight difference (between the disordered and the clean systems, see equation (29)) as a function of the layer index for a system of a single doped Kondo insulator interfaced with (a) 11 clean band-insulators (black); (b) 11 clean Kondo insulators (red) and (c) 11 metallic layers (green). The main panel is the spectral weight difference with a cutoff, $\lambda \rightarrow \infty$. In the inset, $\Omega_{\text{BI}} = \frac{1}{2} \left(-t_{\parallel} + \sqrt{t_{\parallel}^2 + 4V^2} \right)$, representing the hybridization gap edge of an isolated band insulator, has been used as the cutoff (λ) in energy space to get the spectral weight difference at ‘low’ energies ($|\omega| < \Omega_{\text{BI}}$). The dot-dashed lines are algebraic decay fits, with black for (a) and (c), and red for (b). $U = 1.7$ in the Kondo insulating layers, $V = 0.44$ in both the band insulating and Kondo insulating layers, the inter-layer hopping is set to $t_{\perp} = 0.5$.

screen the proximity effects of disorder. However, in the neighborhood of the Fermi level, the presence of a spectral gap makes the band-insulator immune to the changes in the boundary layer, and the presence or absence of interactions is irrelevant.

4. DISCUSSION

For the results in the previous section, it is clear that Kondo hole substitution in a single boundary layer does indeed affect neighboring layers to varying degrees on different energy scales. Although we have considered finite systems, a few general remarks may be made for infinite, periodic structures.

4.1. f -electron Superlattices:

A superlattice structure comprises a periodic array of unit cells, each of which consist of a finite number of $(m)f$ - e^- and $(n)c$ - e^- layers. For example, in Ref. 23, $(m, 4)\text{CeIn}_3/\text{LaIn}_3$ superlattices were grown and m was

tuned. The authors surmised that Kondo hole disorder at the Ce/La interface is inevitable. As shown in figure 9, the extent of proximity induced disorder effects is appreciable in the neighboring layers. Owing to the periodic nature of a superlattice, it is thus expected that this proximity effect would be even more pronounced stemming from penetration of disorder effects from the adjacent unit cells of the superlattice.

4.2. A scenario for disorder induced non-Fermi liquid:

Thus far, we have considered the particle-hole symmetric limit. However, an interesting situation might emerge by varying the chemical potential such that the system does not have particle-hole symmetry. Dynamical effects of impurity scattering even at the single-site mean field level have been shown (in Ref. 27) to lead to a non-Fermi liquid form of the average selfenergy. Thus the Kondo hole disordered layers in such an array of f electron layers would show non-Fermi liquid behavior. The non-Fermi liquid nature of the Kondo hole disordered layers would thus introduce a further anisotropy in the system that would possibly manifest itself in the transport properties of these systems. Moreover, if the Ce/La interfaces in the superlattice unit cell are separated by a larger number of clean layers, the non-Fermi liquid effects would be expected to attenuate. Hence a non-Fermi liquid to Fermi liquid crossover can be expected simply by increasing the ratio of the number of layers to the number of Ce/La interfaces.

4.3. Anderson Localization:

One of the important consequences of disorder, ignored in this work, is that of Anderson localization (AL). The CPA employed here to treat disorder effects is incapable of incorporating AL. The addition of coherent back-scattering and deep trap physics beyond CPA should lead to profound consequences for the adjacent layers. The typical medium -dynamical cluster approximation (TMDCA) developed recently³⁸ has been found to be an excellent approach for obtaining the correct phase diagram of the non-interacting Anderson model. It would be interesting to extend the TMDCA for interacting models and explore the interplay of Anderson localization physics and strong interactions in layered systems.

5. SUMMARY AND CONCLUSIONS

In this work, we have employed the inhomogeneous dynamical mean field theory¹⁹ framework to obtain self consistent many body solutions for layered Kondo hole substituted f -electron systems. The substitutional disorder, treated within the coherent potential approximation,

was introduced in a single boundary layer, and the consequent spectral changes in the neighboring layers were explored. Three distinct types of clean adjacent layers were considered: (a) non-interacting metals (disordered Kondo insulator/metals), (b) non-interacting band insulators (disordered Kondo insulator/band insulator), and, (c) several clean Kondo insulators.

Combining simple analytical expressions for bilayer and trilayer systems with full numerical calculations using the local moment approach, we have (a) explained the strong renormalization of the low energy spectra of the proximal layers, (b) spectral interference among the layers in presence of an inter-layer coupling ($t_{\perp}$), and (c) a mechanism for penetration of Kondo hole disorder induced incoherence into clean layers. We highlight the differences between three distinct types of interfaces with a disordered Kondo insulator layer. We also demonstrate that, in addition to a robust low energy quasiparticle peak²⁰, proximity effects of interactions also manifest through the appearance of minute Hubbard bands in the neighboring non-interacting layers.

A finite concentration of Kondo holes leads to the formation of an impurity band at the Fermi level in a Kondo insulator³⁶, thus creating metallic states in the otherwise gapped insulator. In the layered geometry, these disorder induced metallic states can further tunnel into the immediately neighboring clean Kondo insulator, rendering a quadratic bending in its Kondo hybridization gap edge. This further induces metallic states in the f - e^{-} spectra of the nearest neighbor layer. These disorder induced states do propagate into the further layers but the tunneling is attenuated by the ω^2 factor for each layer and hence is too small to be observed beyond the nearest neighbor layer. Introduction of disorder further destroys the proximity effect of interactions. We showed that a manifestation of proximity induced interaction effect, on the adjacent non-interacting layers, is the appearance of tiny Hubbard bands and a proximal Kondo effect induced

low frequency spectral renormalization. This proximity effect of interactions, on the non-interacting layers, is mitigated when they are coupled to a disordered Kondo insulator layer.

The presence of disorder induces spectral weight transfer from the high energy Hubbard bands to the low energy Kondo scaling regime not only in the disordered Kondo insulator but in the adjacent clean layers as well. We have quantified the penetration of disorder effects in these interfaces through the spectral weight difference function (equation (29)). The spectral weight difference is maximum in the disordered Kondo insulator and decays algebraically with distance from the disordered Kondo insulator layer.

Our analysis implies that, while for thin films, the spectral weight difference of the clean layers is appreciable only until the third neighboring layer; for superlattice geometries, this effect of penetration of disorder would be quite pronounced due to the occurrence of multiple disordered interfaces.

We foresee a Fermi liquid to non-Fermi liquid crossover in the transport properties across disordered interfaces by tuning the number of disordered layers. The full study of such a crossover and inclusion of localization effects beyond the coherent potential approximation will be the subjects of future projects.

ACKNOWLEDGMENTS

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¹ A. Ohtomo, D. Muller, J. Grazul, and H. Hwang, *Nature* **419**, 378 (SEP 26 2002)

² K. Yoshimatsu, T. Okabe, H. Kumigashira, S. Okamoto, S. Aizaki, A. Fujimori, and M. Oshima, *Phys. Rev. Lett.* **104**, 147601 (Apr 2010)

³ K. Yoshimatsu, K. Horiba, H. Kumigashira, T. Yoshida, A. Fujimori, and M. Oshima, *Science* **333**, 319 (2011)

⁴ S. Okamoto, *Phys. Rev. B* **84**, 201305 (Nov 2011)

⁵ M. Potthoff and W. Nolting, *Physica B* **259**, 760 (1999)

⁶ N. Reyren, S. Thiel, A. D. Caviglia, L. F. Kourkoutis, G. Hammerl, C. Richter, C. W. Schneider, T. Kopp, A.-S. Retschi, D. Jaccard, M. Gabay, D. A. Muller, J.-M. Triscone, and J. Mannhart, *Science* **317**, 1196 (2007)

⁷ J. A. Bert, B. Kalisky, C. Bell, M. Kim, Y. Hikita, H. Y. Hwang, and K. A. Moler, *Nature Physics* **7**, 767 (2011)

⁸ X. W. Ariando, G. Baskaran, Z. Q. Liu, J. Huijben, J. B. Yi, A. Annadi, A. R. Barman, A. Rusydi, S. Dhar, Y. P.

Feng, J. Ding, H. Hilgenkamp, and T. Venkatesan, *Nature Communications* **2** (2011)

⁹ P. Zubko, S. Gariglio, M. Gabay, P. Ghosez, and J.-M. Triscone, *Ann. Rev. Condens. Matter Phys.* **2**, 141 (Jan 2011)

¹⁰ M. Potthoff and W. Nolting, *Phys. Rev. B* **60**, 7834 (Sep 1999) S. Schwieger, M. Potthoff, and W. Nolting, *ibid.* **67**, 165408 (Apr 2003) M. Potthoff and W. Nolting, *The European Physical Journal B* **8**, 555 (1999) *Phys. Rev. B* **59**, 2549 (Jan 1999) *Journal of Physics: Condensed Matter* **8**, 4937 (1996)

¹¹ S. Okamoto and A. J. Millis, *Phys. Rev. B* **70**, 241104 (Dec 2004) *Physica B: Condensed Matter* **359-361**, 1378 (2005), ISSN 0921-4526 *Phys. Rev. B* **72**, 235108 (Dec 2005)

¹² H. Zenia, J. K. Freericks, H. R. Krishnamurthy, and T. Pruschke, *Phys. Rev. Lett.* **103**, 116402 (Sep 2009)

- ¹³ A. Euverte, F. Hébert, S. Chiesa, R. T. Scalettar, and G. G. Batrouni, Phys. Rev. Lett. **108**, 246401 (Jun 2012)
- ¹⁴ H. Ishida and A. Liebsch, Phys. Rev. B **79**, 045130 (Jan 2009)
- ¹⁵ H. Ishida and A. Liebsch, Phys. Rev. B **82**, 045107 (Jul 2010)
- ¹⁶ H. Ishida and A. Liebsch, Phys. Rev. B **85**, 045112 (Jan 2012)
- ¹⁷ R. W. Helmes, T. A. Costi, and A. Rosch, Phys. Rev. Lett. **101**, 066802 (Aug 2008)
- ¹⁸ A. Rüegg, S. Pilgram, and M. Sigrist, Phys. Rev. B **75**, 195117 (May 2007) **77**, 245118 (Jun 2008)
- ¹⁹ J. K. Freericks, Phys. Rev. B **70**, 195342 (Nov 2004)
- ²⁰ R. Peters, Y. Tada, and N. Kawakami, Phys. Rev. B **88**, 155134 (Oct 2013)
- ²¹ Y. Tada, R. Peters, and M. Oshikawa, Phys. Rev. B **88**, 235121 (Dec 2013)
- ²² S. Okamoto and T. A. Maier, Phys. Rev. Lett. **101**, 156401 (Oct 2008)
- ²³ H. Shishido, T. Shibauchi, K. Yasu, T. Kato, H. Kontani, T. Terashima, and Y. Matsuda, Science **327**, 980 (FEB 19 2010)
- ²⁴ R. Peters and N. Kawakami, Phys. Rev. B **89**, 041106 (Jan 2014)
- ²⁵ C. Grenzebach, F. B. Anders, G. Czycholl, and T. Pruschke, Phys. Rev. B **77**, 115125 (Mar 2008)
- ²⁶ M. Shimozawa, T. Watashige, S. Yasumoto, Y. Mizukami, M. Nakamura, H. Shishido, S. K. Goh, T. Terashima, T. Shibauchi, and Y. Matsuda, Phys. Rev. B **86**, 144526 (Oct 2012)
- ²⁷ N. S. Vidhyadhiraja and P. Kumar, Phys. Rev. B **88**, 195120 (Nov 2013)
- ²⁸ E. Feenberg, Phys. Rev. **74**, 206 (Jul 1948) E. N. Economou, *Green's Functions in Quantum Physics* (Springer; 3rd edition, 2006)
- ²⁹ N. S. Vidhyadhiraja, V. E. Smith, D. E. Logan, and H. R. Krishnamurthy, Journal of Physics: Condensed Matter **15**, 4045 (2003)
- ³⁰ N. S. Vidhyadhiraja and D. E. Logan, European Physical Journal B **39**, 313 (2004), ISSN 1434-6028
- ³¹ D. E. Logan and N. S. Vidhyadhiraja, Journal of Physics: Condensed Matter **17**, 2935 (2005)
- ³² N. S. Vidhyadhiraja and D. E. Logan, Journal of Physics: Condensed Matter **17**, 2959 (2005)
- ³³ W.-C. Yueh, Applied Mathematics E-Notes **5**, 66 (2005)
- ³⁴ M. Potthoff, *Correlated electrons at metal surfaces*, Habilitation Thesis, Humboldt-Universitt zu Berlin, Berlin (1999)
- ³⁵ P. Aynajian, E. H. da Silva Neto, A. Gyenis, R. E. Baumbach, J. D. Thompson, Z. Fisk, E. D. Bauer, and A. Yazdani, Nature **486**, 201 (2012)
- ³⁶ P. Schlottmann, Phys. Rev. B **54**, 12324 (Nov 1996) P. S. Riseborough, **68**, 235213 (Dec 2003) T. Mutou, **64**, 165103 (Sep 2001)
- ³⁷ P. Schlottmann, Phys. Rev. B **46**, 998 (Jul 1992)
- ³⁸ C. E. Ekuma, H. Terletska, K.-M. Tam, Z.-Y. Meng, J. Moreno, and M. Jarrell, Phys. Rev. B **89**, 081107 (Feb 2014)